

# InAsSb photodiode

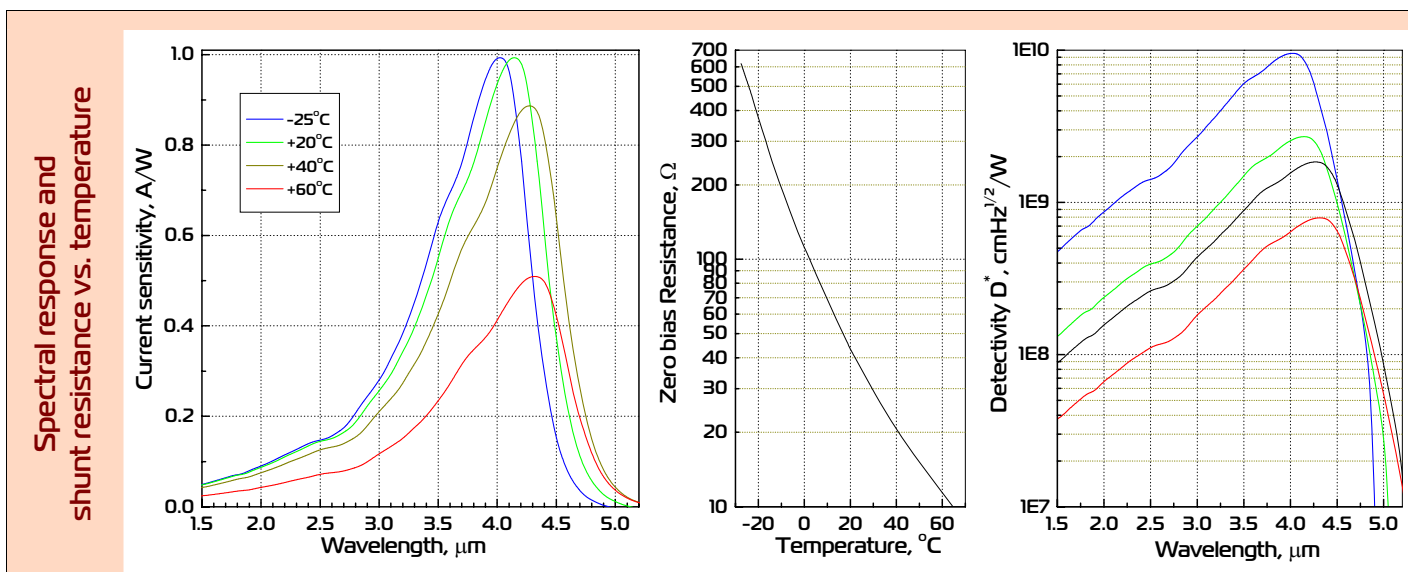
# PD42fs mIL

Peak wavelength	$\lambda$	$\mu\text{m}$	4.15±0.05
Spectral response range	$\lambda_{0.1}$	$\mu\text{m}$	2.0÷4.7
Current sensitivity	$S_i$	A/W	0.8÷1.0
Resistance at zero bias	$R_0$	Ohm	≥40
Detectivity	$D^*_{\lambda_{\text{max}}}$	$\text{cmHz}^{1/2}\text{W}^{-1}$	≥3×10 <sup>9</sup>
Voltage sensitivity	$S_u$	V/W	≥40
Switching time	$\tau$	ns	<50*

\* - according estimation

Model	Package	Lens material; Cap with window	Sensitive area, mm	Angle of view FWHM, deg.	Operation conditions, °C	Polarity
PD42fs mILTO18	TO18	Chalcogenide glass	∅ 1.0	≥60	-25÷+60	Leg near key is negative
PD42fs mILTO18c	TO18	Chalcogenide glass; Sapphire		50		

	PD42fs mILTO18	PD42fs mILTO18c
<b>Product view</b>		
<b>Features</b>	<p>Growth of narrow gap semiconductor alloys onto n<sup>-</sup>-InAs substrate; "Wide gap" window; Optical coupling through the use of chalcogenide glass lenses</p> <p>Data are valid for 22°C. Photodiode could be equipped with preamplifier that is designed for conversion of PD photocurrent into a convenient output voltage and is adjusted for the particular PD taking into account the R<sub>0</sub> value and frequency range. Other packages are available upon request</p>	<p>Ambient and high temperature operation; No bias required; Short time constant; High value of shunt resistance; Operation from DC to VHF; Highest long term stability</p>



Product specifications are subject to change without prior notice due to improvements or other reasons. Updated 23.10.12



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